Ordering number:EN1799D

NPN Epitaxial Planar Silicon Transistor



## 2SC3576

# High hfe, Low-Frequency General-Purpose Amplifier Applications

## **Applications**

· LF general-purpose amplifiers, various drivers, muting circuit.

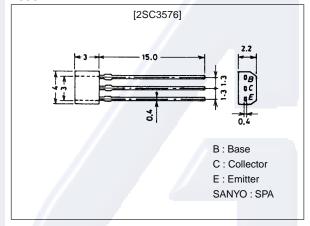
#### **Features**

- · Adoption of FBET process.
- · High DC current gain (h<sub>FE</sub>=800 to 3200).
- · Low collector-to-emitter saturation voltage  $(V_{CE(sat)} \le 0.5V)$ .
- · High  $V_{EBO}$  ( $V_{EBO} \ge 15V$ ).

## **Package Dimensions**

unit:mm

2033



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>СВО</sub>		30	V
Collector-to-Emitter Voltage	VCEO		25	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		15	V
Collector Current	l <sub>C</sub>		300	mA
Collector Current (Pulse)	I <sub>CP</sub>		500	mA
Base Current	ΙB		60	mA
Collector Dissipation	PC		300	mW
Junction Temperature	Tj	279 1 1	150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =20V, I <sub>E</sub> =0			0.1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =10V, I <sub>C</sub> =0			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	800	1500	3200	
Gain-Bandwidth Product	fΤ	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA		250		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		2.7		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =4mA		0.12	0.5	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =4mA		0.85	1.2	V

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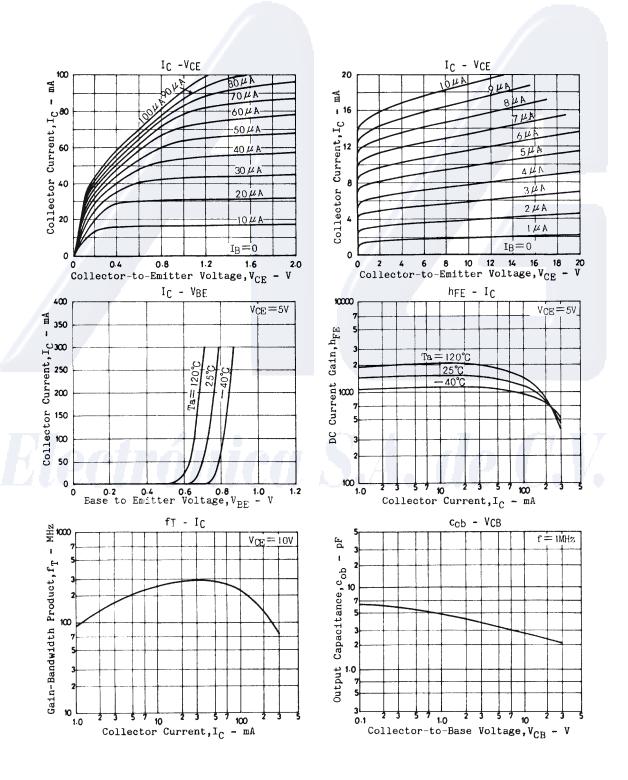
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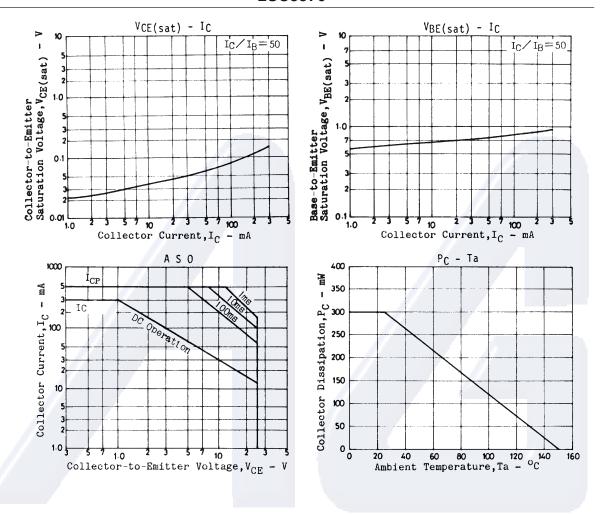
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#### 2SC3576

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	25			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	15			V



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